

HAT2054M

Silicon N Channel Power MOS FET
Power Switching

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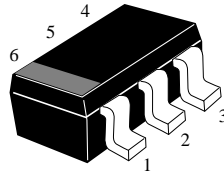
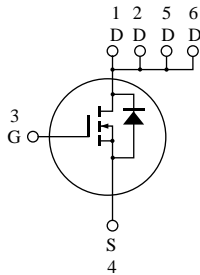
ADE-208-756B (Z)
Preliminary 3rd. Edition
Dec. 1998

Features

- Low on-resistance
- Low drive current
- High density mounting
- 4.5V gate drive device can be driven from 5V source

Outline

TSOP-6



4 Source
3 Gate
1, 2, 5, 6 Drain

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D^{*2}	6.3	A
Drain peak current	$I_{D(pulse)}^{*1}$	25.2	A
Body-drain diode reverse drain current	I_{DR}^{*2}	6.3	A
Channel dissipation	$Pch_{(pulse)}^{*2}$	2.0	W
	$Pch_{(continuous)}^{*3}$	1.05	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$

2. When using the alumina ceramic board (50 x 50 x 0.7 mm), $PW = 5s$, $T_a = 25^\circ C$

3. When using the alumina ceramic board (50 x 50 x 0.7 mm), $T_a = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

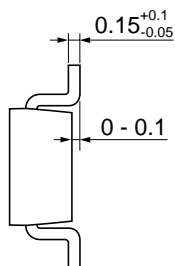
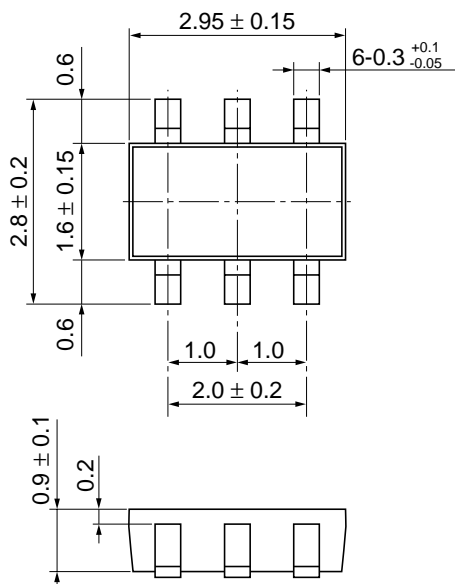
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10mA$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	±0.1	μA	$V_{GS} = \pm 20V$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 30V$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$V_{DS} = 10V$, $I_D = 1mA$
Static drain to source on state resistance	$R_{DS(on)}$	—	26	31	mΩ	$I_D = 3A$, $V_{GS} = 10V^{*1}$
	$R_{DS(on)}$	—	40	52	mΩ	$I_D = 3A$, $V_{GS} = 4.5V^{*1}$
Forward transfer admittance	$ y_{fs} $	4	7	—	S	$I_D = 3A$, $V_{DS} = 10V^{*1}$
Input capacitance	Ciss	—	620	—	pF	$V_{DS} = 10V$
Output capacitance	Coss	—	170	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	110	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	13	—	ns	$V_{GS} = 10V$, $I_D = 3A$
Rise time	t_r	—	90	—	ns	$R_L = 3.3\Omega$
Turn-off delay time	$t_{d(off)}$	—	50	—	ns	
Fall time	t_f	—	40	—	ns	
Body-drain diode forward voltage	V_{DF}	—	0.95	—	V	$IF = 6.3A$, $V_{GS} = 0^{*1}$
Body-drain diode reverse recovery time	t_{rr}	—	(50)	—	ns	$IF = 6.3A$, $V_{GS} = 0$ $diF/dt = 20A/\mu s$

Note: 1. Pulse test

Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TSOP-6
JEDEC	—
EIAJ	—
Mass (reference value)	0.012 g

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